WANSEMI
万芯半导体

WP4N60KD

Enhancement Mode N-Channel Power MOSFET

TO-252/NMOS/600V/±30V/3V/4A/1.9Ω

Rev0.3

600V,1.9Ω, 4A, N-Channel MOSFET

1.Features

- New technology for high voltage device
- Low on-resistance and low conduction losses
- Ultra Low Gate Charge cause lower driving requirements

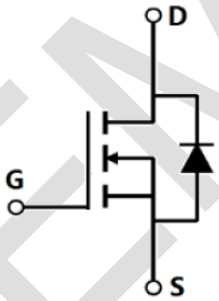
V_{DS} Typ.	$R_{DS(on)}$ Typ.	I_D Max.
600V	1.9Ω @ 10V	4A

2.Applications

- Power factor correction
- Switched mode power supplies
- Uninterruptible Power Supply

Pin Description

TO-252



Schematic Diagram

3.Package Marking and Ordering Information

Part no.	Marking	Package	PCS/Reel	PCS/CTN.
WP4N60KD	WP4N60KD	TO-252	2,500	25,000

4.Absolute Max Ratings at Ta=25℃ (Note1)

Parameter	Symbol	Maximum	Units
Drain to Source Voltage	V_{DSS}	600	V
Gate to Source Voltage	V_{GSS}	±30	V
Drain Current-Continuous	I_D	4	A
Drain Current (Pulse)	I_{DM}	16	A
Single Pulsed Avalanche Energy	E_{AS}	245	mJ
Maximum Power Dissipation	P_D	104	W
Operating Junction and Storage Temperature Range	T_j, T_{stg}	-55 to +160	℃

Note 1: Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

5.Thermal Resistance Ratings (Note 2)

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	1.2	℃/W

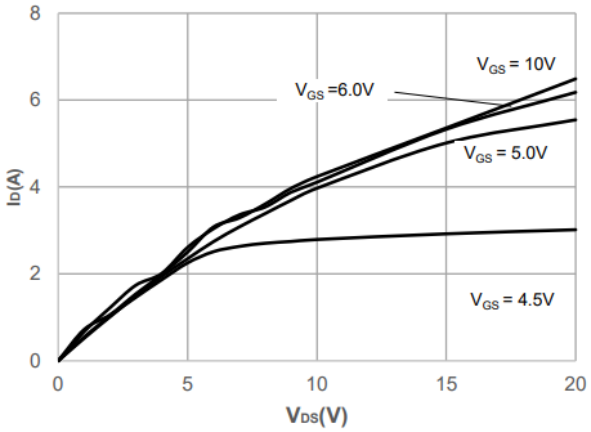
Note 2: When mounted on 1 inch square copper board t ≤ 10sec The value in any given application depends on the user's specific board design.

6.Electrical Characteristics at Ta=25℃ (Note 3)

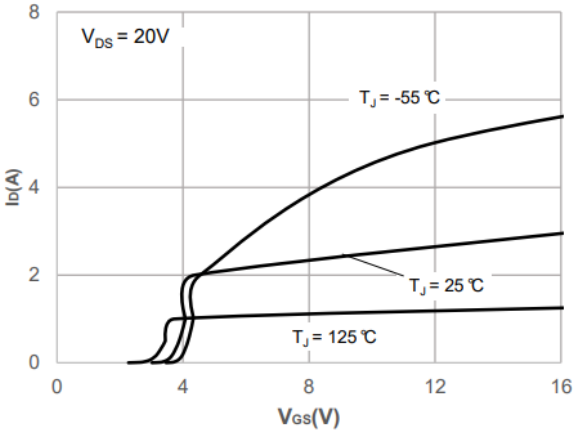
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Drain to Source Breakdown Voltage	$V_{(BR)DSS}$	I_D = 250μA, V_{GS} = 0V	600			V
Zero-Gate Voltage Drain Current	I_{DSS}	V_{DS} = 600V, V_{GS} = 0V			1	μA
Gate-Body Leakage Current	I_{GSS}	V_{GS} = ±20V, V_{DS} = 0V			±100	nA
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS}, I_{DS}=250μA	2.4	3.0	4.0	V
Drain to Source On-State Resistance	$R_{DS(on)}$	I_D = 2A, V_{GS} = 10V		1.9	2.2	Ω
Input Capacitance	C_{iss}	V_{GS}=0V, V_{DS}=25V, Frequency=1.0MHz		607		pF
Output Capacitance	C_{oss}			61		pF
Reverse Transfer Capacitance	C_{rss}			10		pF
Turn-ON Delay Time	$t_{d(on)}$	V_{DD} = 300V, V_{GS} = 10V, R_{GEN} = 24Ω,I_D = 2A		12		ns
Turn-ON Rise Time	t_r			18		ns
Turn-OFF Delay Time	$t_{d(off)}$			49		ns
Turn-ON Fall Time	t_f			27		ns
Total Gate Charge	Q_g	V_{DS} = 300V, V_{GS} = 10V, I_D = 2A		14		nC
Gate-Source Charge	Q_{gs}			3.2		nC
Gate-Drain Charge	Q_{gd}			4.4		nC
Diode Forward Voltage	V_{SD}	I_S = 4A, V_{GS} = 0V	0.55	0.8	1.1	V
Maximum Continuous Drain to Source Diode Forward Curren	I_S	-	-	-	4	A
Maximum Pulsed Drain to Source Diode Forward Current	I_{SM}	-	-	-	16	A
Body Diode Reverse Recovery Time	t_{rr}	I_F=4A, di/dt=100A/μs	-	290	-	nS
Body Diode Reverse Recovery Charg	Q_{rr}		-	0.8	-	nC

Note 3: Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

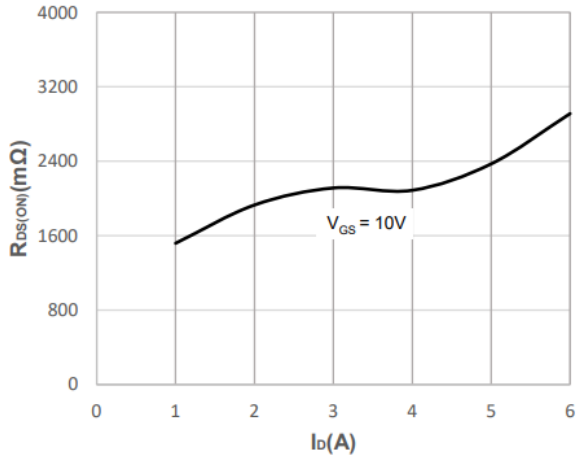
7.Typical electrical and thermal characteristics



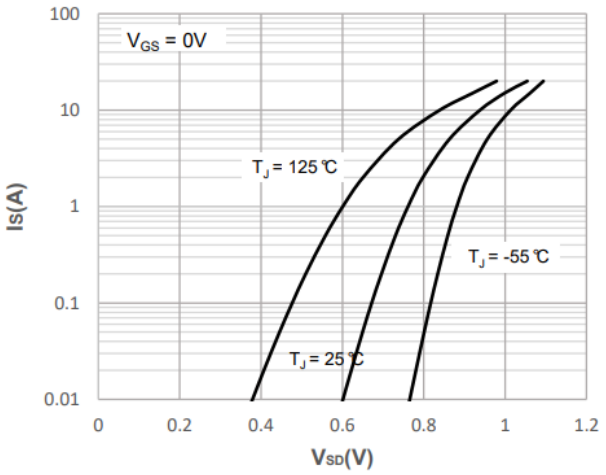
Output Characteristics



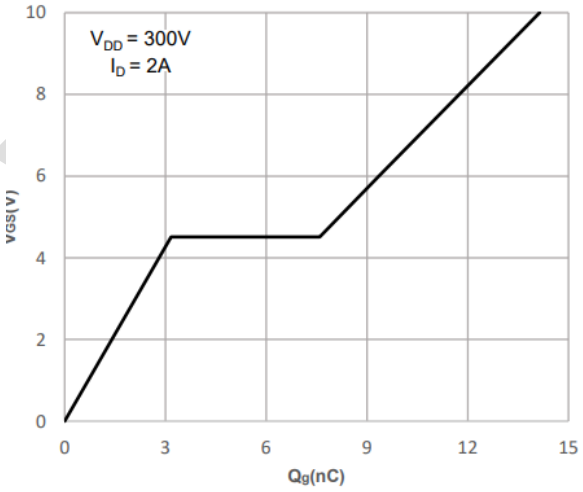
Typical Transfer Characteristics



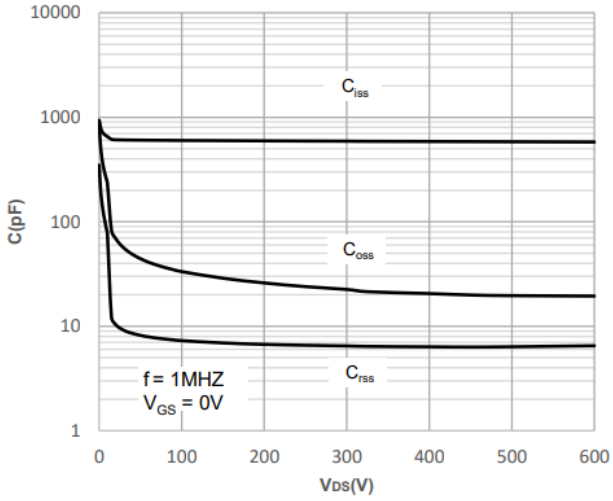
Static drain-source on resistance



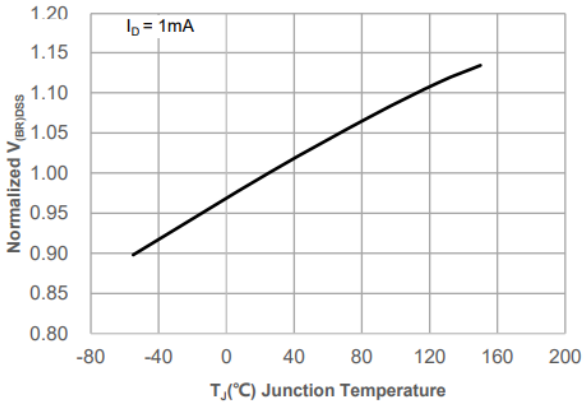
Body Diode Characteristics



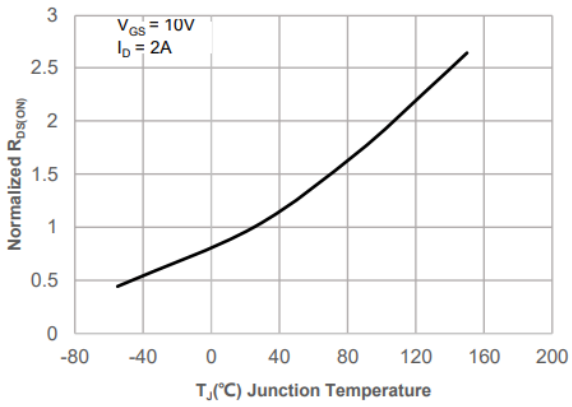
Gate Charge Characteristics



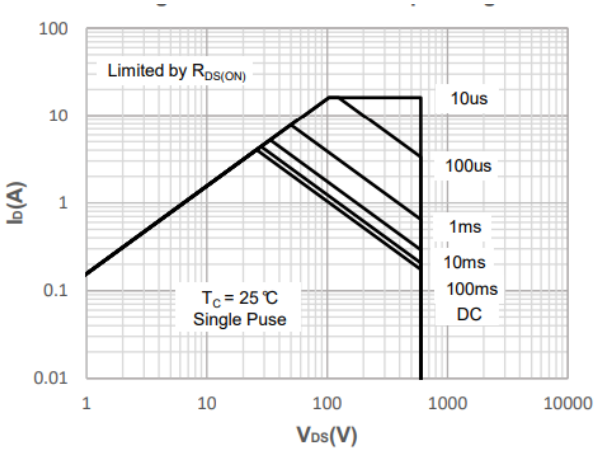
Capacitance Characteristics



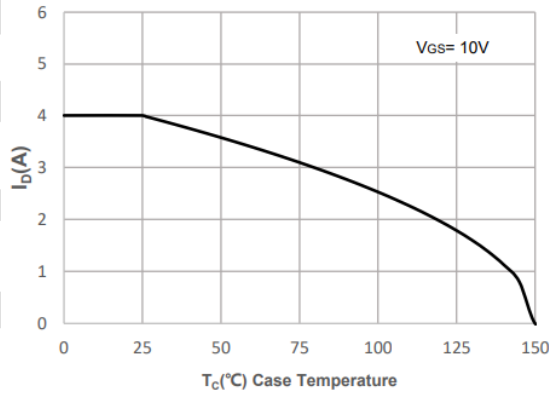
Normalized Breakdown Voltage vs . Junction Temperature



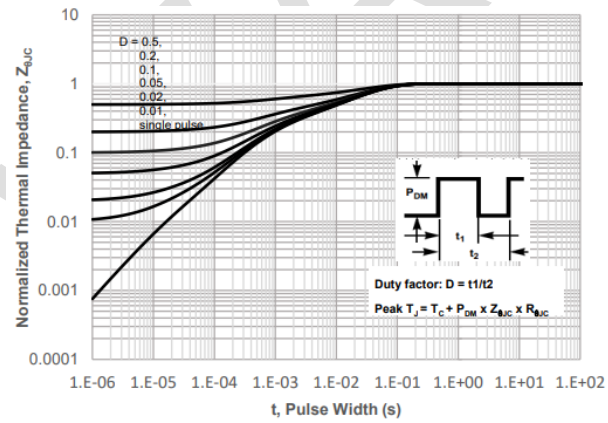
Normalized on Resistance vs . Junction Temperature



Safe operating area

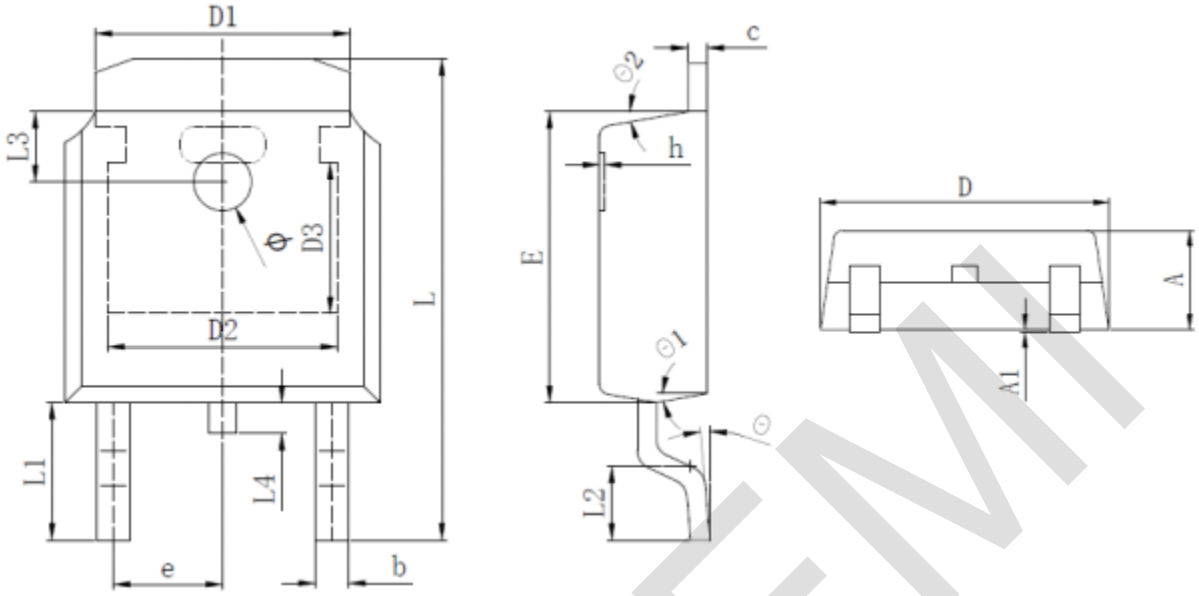


Maximum Continuous Drain Current vs. Case Temperatur



Maximum Continuous Drain Current vs. Case Temperature

8.Package Dimensions



SYMBOL	MILLIMETER		
	MIN	Typ.	MAX
A	2.200	2.300	2.400
A1	0.000		0.127
b	0.640	0.690	0.740
c(电镀后)	0.460	0.520	0.580
D	6.500	6.600	6.700
D1	5.334 REF		
D2	4.826 REF		
D3	3.166 REF		
E	6.000	6.100	6.200
e	2.286 TYP		
h	0.000	0.100	0.200
L	9.900	10.100	10.300
L1	2.888 REF		
L2	1.400	1.550	1.700
L3	1.600 REF		
L4	0.600	0.800	1.000
Φ	1.100	1.200	1.300
θ	0°		8°
θ1	9° TYP		
θ2	9° TYP		

9.Important Notice

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